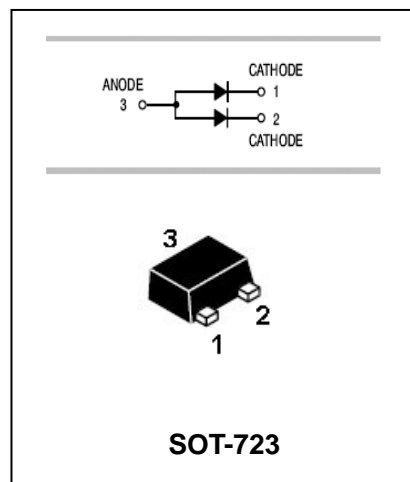


## Surface mount switching diode

## BAW56M

### FEATURES

- For General Purpose switching Applications.
- Fast Switching Speed.
- High Conductance.
- Surface Mount Package Ideally Suited for Automatic Insertion.



### APPLICATIONS

- High speed switching application.

### ORDERING INFORMATION

Type No.	Marking	Package Code
BAW56M	A1	SOT-723

### MAXIMUM RATING @ Ta=25°C unless otherwise specified

Characteristic	Symbol	Limits	Unit
Non-repetitive peak reverse voltage	$V_{RM}$	100	V
Peak Repetitive Reverse Voltage Working peak reverse voltage DC Reverse Voltage	$V_{RRM}$ $V_{RWM}$ $V_R$	75	V
Continuous Forward Current Single diode loaded Double diode loaded	$I_F$	215 125	mA
Non-repetitive forward Surge Current @t=1.0ms @t=1.0s	$I_{FSM}$	1 0.5	A
Power Dissipation	$P_D$	150	mW
Thermal resistance junction to ambient air	$R_{\theta JA}$	357	°C/W
Operating Junction Temperature Range	$T_j$	150	°C
Storage Temperature Range	$T_{STG}$	-65 to +150	°C

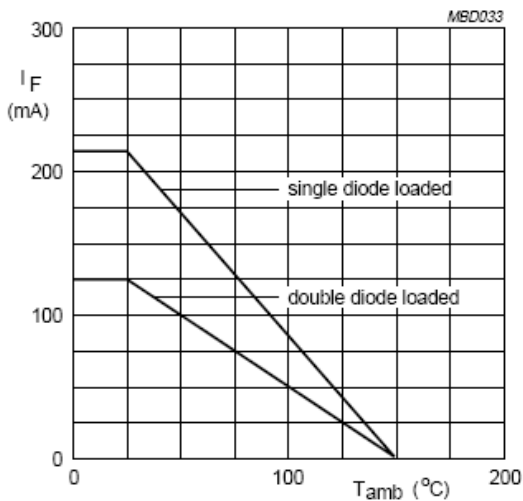
Surface mount switching diode

**BAW56M**

ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

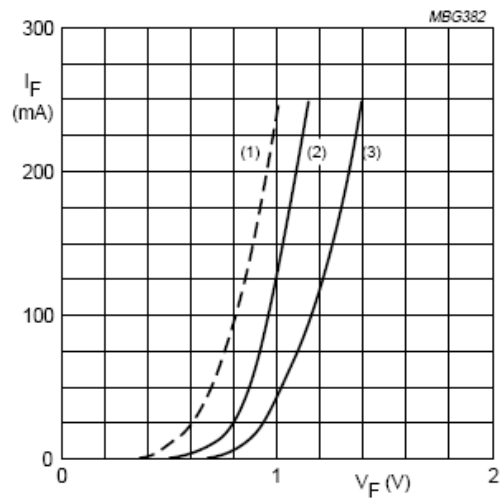
Characteristic	Symbol	Min	MAX	UNIT	Test Condition
Reverse Breakdown Voltage	$V_{(BR)R}$	75	-	V	$I_R = 2.5\mu A$
Forward Voltage	$V_F$	-	0.715 0.855 1.0 1.25	V	$I_F = 1mA$ $I_F = 10mA$ $I_F = 50mA$ $I_F = 150mA$
Reverse Leakage Current	$I_R$	-	2.5 25	$\mu A$ nA	$V_R = 75V$ $V_R = 20V$
Diode Capacitance	$C_D$	-	2	pF	$V_R = 0V, f = 1MHz$
Reverse Recovery Time	$t_{rr}$	-	4	ns	$I_F = I_R = 10mA,$ $I_{rr} = 0.1 * I_R, R_L = 100\Omega$

TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified



Device mounted on an FR4 printed-circuit board.

Fig.1 Maximum permissible continuous forward current as a function of ambient temperature.

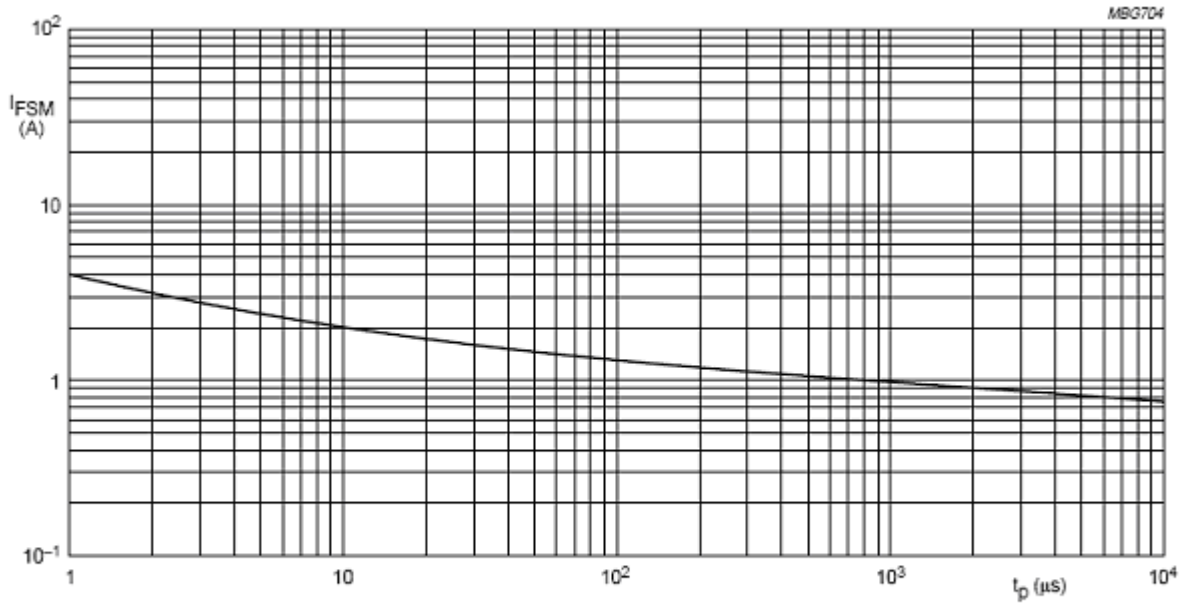


- (1)  $T_j = 150^\circ C$ ; typical values.
- (2)  $T_j = 25^\circ C$ ; typical values.
- (3)  $T_j = 25^\circ C$ ; maximum values.

Fig.2 Forward current as a function of forward voltage.

Surface mount switching diode

**BAW56M**



Based on square wave currents.  
 $T_j = 25\text{ }^{\circ}\text{C}$  prior to surge.

Fig.3 Maximum permissible non-repetitive peak forward current as a function of pulse duration.

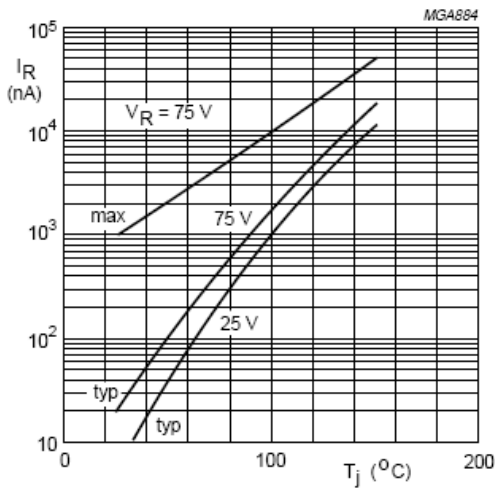
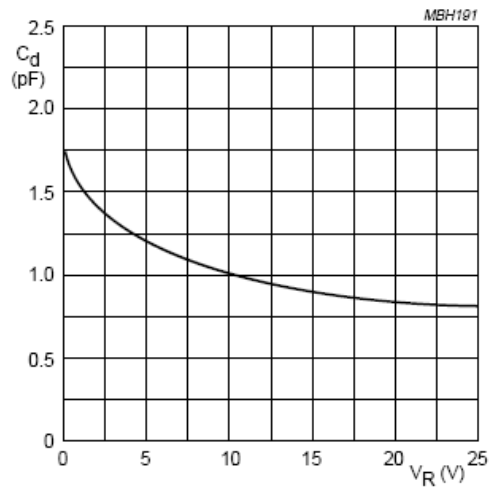


Fig.4 Reverse current as a function of junction temperature.



$f = 1\text{ MHz}$ ;  $T_j = 25\text{ }^{\circ}\text{C}$ .

Fig.5 Diode capacitance as a function of reverse voltage; typical values.

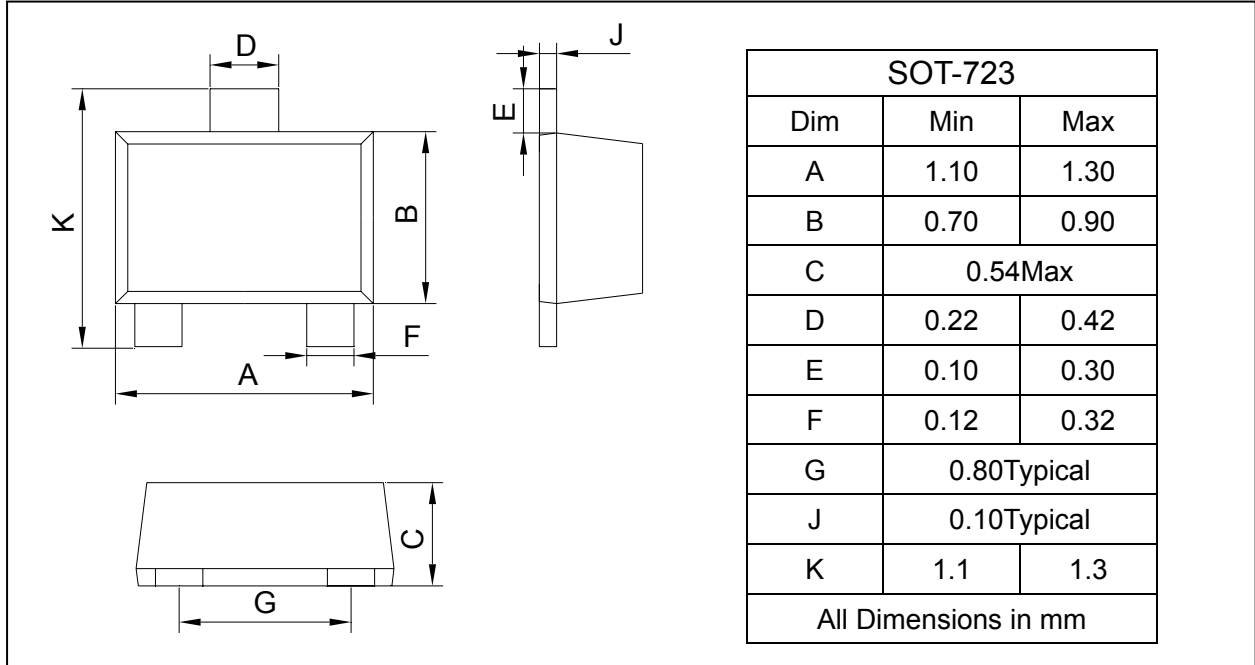
Surface mount switching diode

**BAW56M**

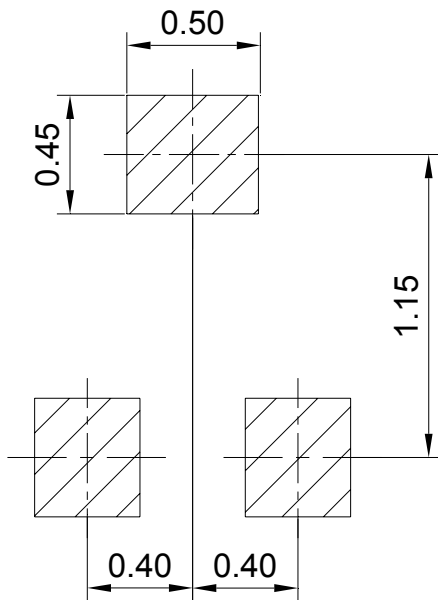
PACKAGE OUTLINE

Plastic surface mounted package

SOT-723



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
BAW56M	SOT-723	10000/Tape&Reel